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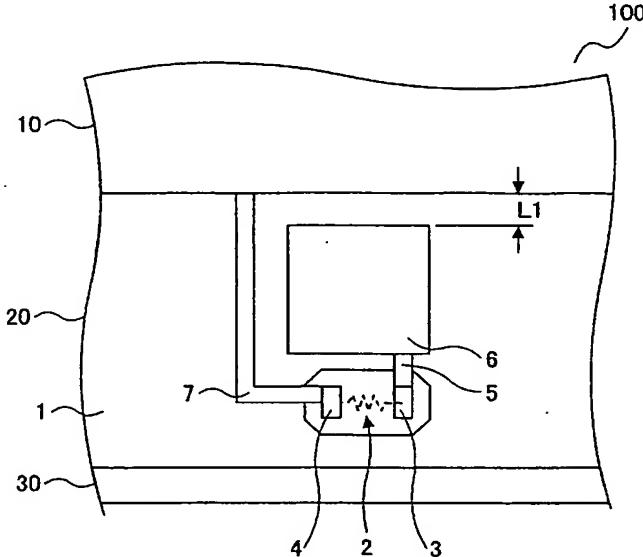
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(54) Title: A SEMICONDUCTOR APPARATUS



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(57) Abstract: A semiconductor apparatus is disclosed. The semiconductor apparatus comprises a substrate with a pad, an internal circuitry region, and a protection resistance formed on the substrate. The pad is connected to a first electrode of the protection resistance by wiring, the internal circuitry region is connected to a second electrode of the protection resistance by wiring, and the protection resistance protects the internal circuitry region from electrostatic discharging. The semiconductor apparatus is characterized in that the pad is placed between the protection resistance and the internal circuitry region.



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